

ESD protected N-Channel Enhancement Mode MOSFET

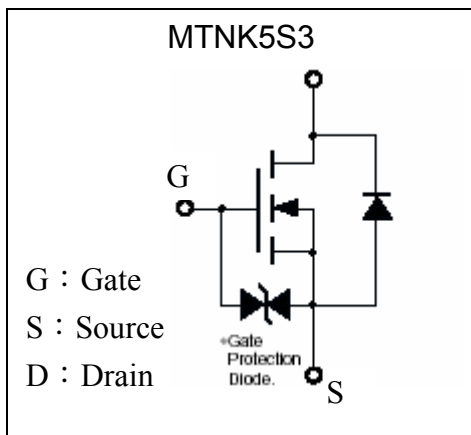
MTNK5S3

| | |
|-------------------|------------|
| BV_{DSS} | 30V |
| I_D | 100mA |
| $R_{DS(on)(MAX)}$ | 8 Ω |

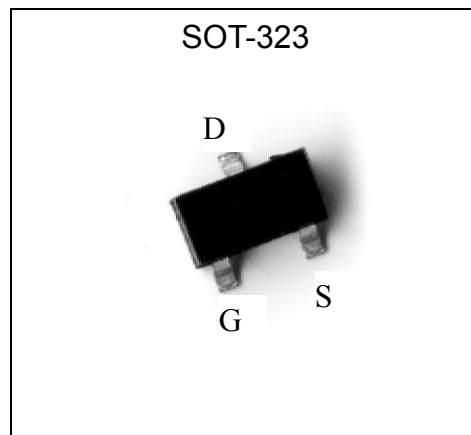
Description

- Low voltage drive(2.5V drive) makes this device ideal for portable equipment.
- High speed switching
- ESD protected device
- Pb-free lead plating & halogen-free package

Symbol



Outline



Ordering Information

| Device | Package | Shipping |
|----------------|--|------------------------|
| MTKN5S3-0-T1-G | SOT-323 (Pb-free lead plating & halogen-free package) | 3000 pcs / Tape & Reel |



Absolute Maximum Ratings (Ta=25°C)

| Parameter | | Symbol | Limits | Unit |
|--|------------|-----------------------------------|----------|------|
| Drain-Source Voltage | | BV _{DSS} | 30 | V |
| Gate-Source Voltage | | V _{GS} | ±20 | V |
| Drain Current | Continuous | I _D | ±100 | mA |
| | Pulsed | I _{DP} | ±200 *1 | mA |
| Reverse Drain Current | Continuous | I _{DR} | ±100 | mA |
| | Pulsed | I _{DRP} | ±200 *1 | mA |
| Total Power Dissipation | | P _D | 200 *2 | mW |
| ESD susceptibility | | | 750 *3 | V |
| Operating Junction and Storage Temperature Range | | T _j ; T _{stg} | -55~+150 | °C |
| Thermal Resistance, Junction-to-Ambient | | R _{th,ja} | 556 | °C/W |

Note : *1. Pulse Width ≤ 10μs, Duty cycle ≤1%
 *2. With each pin mounted on the recommended lands.
 *3. Human body model, 1.5kΩ in series with 100pF

Electrical Characteristics (Ta=25°C)

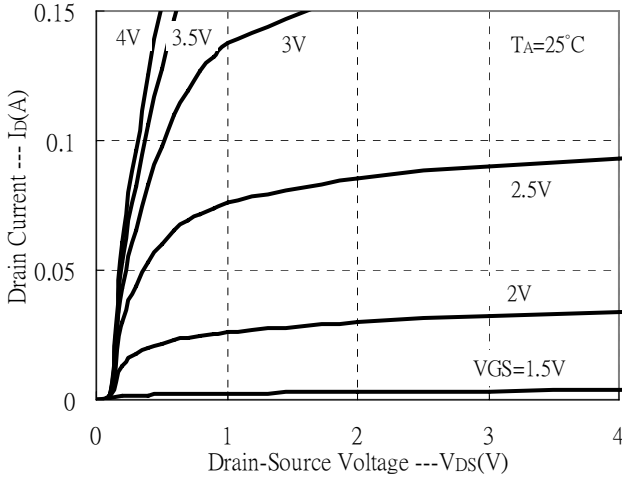
| Symbol | Min. | Typ. | Max. | Unit | Test Conditions |
|---------------------------|------|------|------|------|--|
| Static | | | | | |
| BV _{DSS} | 30 | - | - | V | V _{GS} =0, I _D =100μA |
| V _{GS(th)} | 0.8 | 1.3 | 1.5 | V | V _{DS} =3V, I _D =100μA |
| I _{GSS} | - | - | ±1 | μA | V _{GS} =±20V, V _{DS} =0 |
| I _{DSS} | - | - | 100 | nA | V _{DS} =30V, V _{GS} =0 |
| R _{DSON} | - | 3.4 | 8 | Ω | V _{GS} =4V, I _D =10mA |
| | - | 6.9 | 13 | | V _{GS} =2.5V, I _D =1mA |
| G _{FS} | 20 | 50 | - | mS | V _{DS} =3V, I _D =10mA |
| Dynamic | | | | | |
| C _{iss} | - | 12.5 | - | pF | V _{DS} =5V, V _{GS} =0, f=1MHz |
| C _{oss} | - | 7.3 | - | | |
| C _{rss} | - | 3.5 | - | | |
| t _{d(on)} | - | 15 | - | ns | V _{DD} ≐ 5V, I _D =10mA, V _{GS} =5V, R _L =500Ω, R _G =10Ω |
| t _r | - | 35 | - | | |
| t _{d(off)} | - | 75 | - | | |
| t _f | - | 75 | - | | |
| Source-Drain Diode | | | | | |
| *V _{SD} | - | 0.88 | 1.2 | V | V _{GS} =0V, I _S =100mA |

*Pulse Test : Pulse Width ≤300μs, Duty Cycle ≤2%

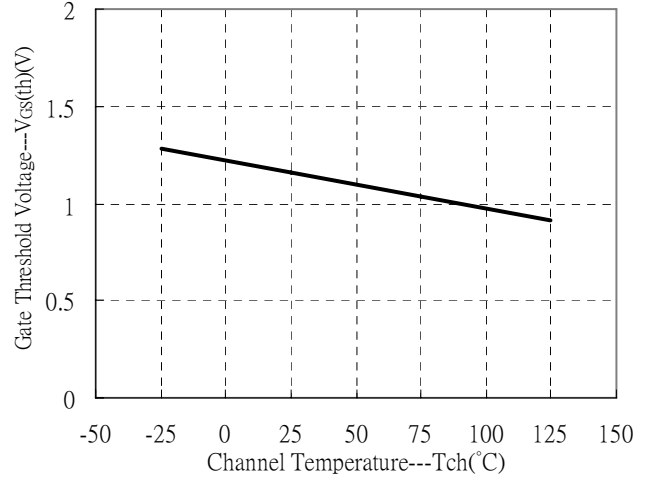


Typical Characteristics

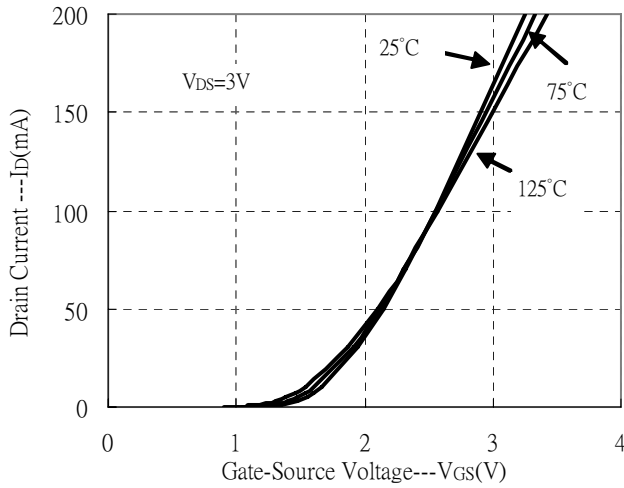
Typical Output Characteristics



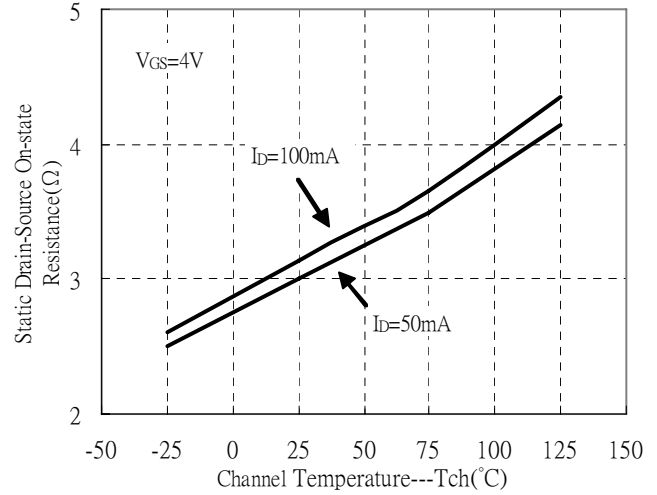
Gate Threshold Voltage vs Channel Temperature



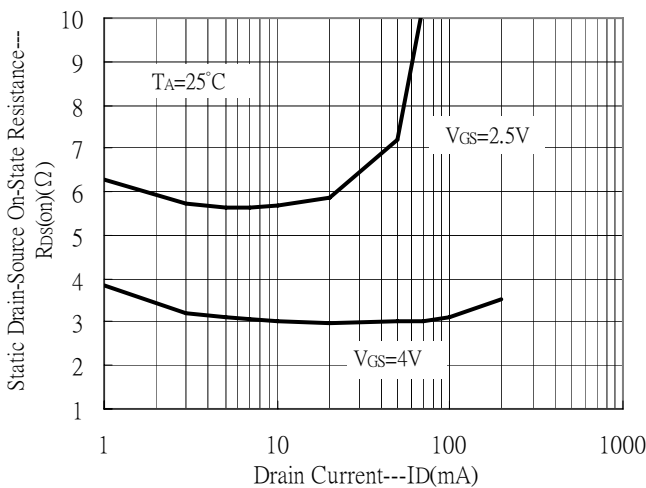
Typical Transfer Characteristics



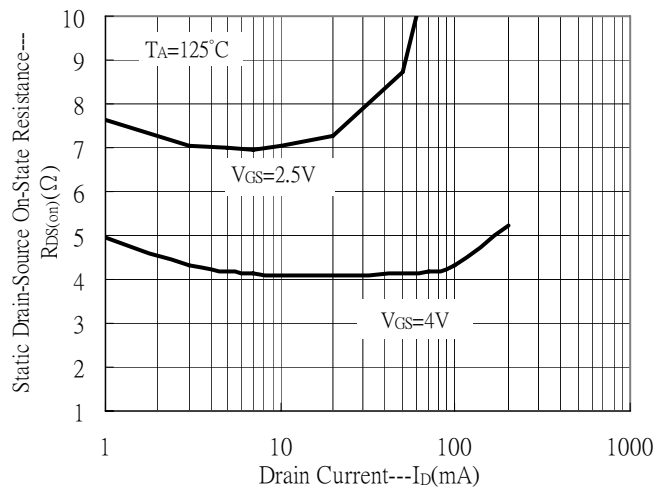
Static Drain-Source On-state Resistance with Temperature



Static Drain-Source On-State resistance vs Drain Current

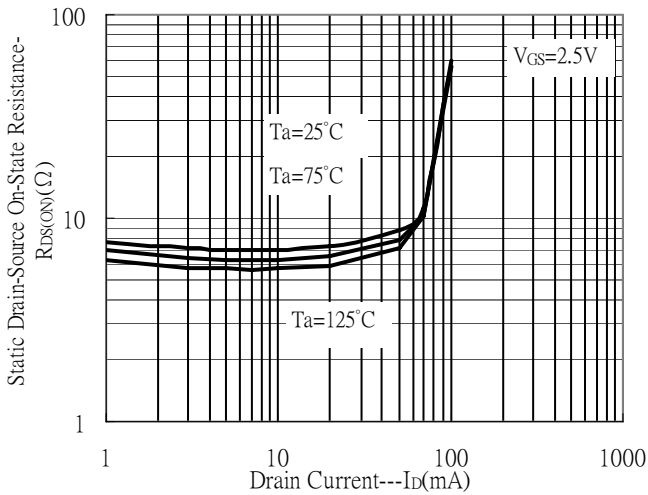


Static Drain-Source On-State resistance vs Drain Current

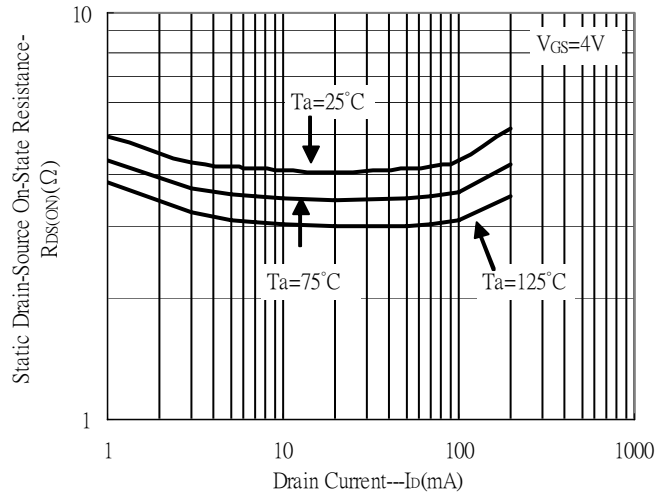


Typical Characteristics(Cont.)

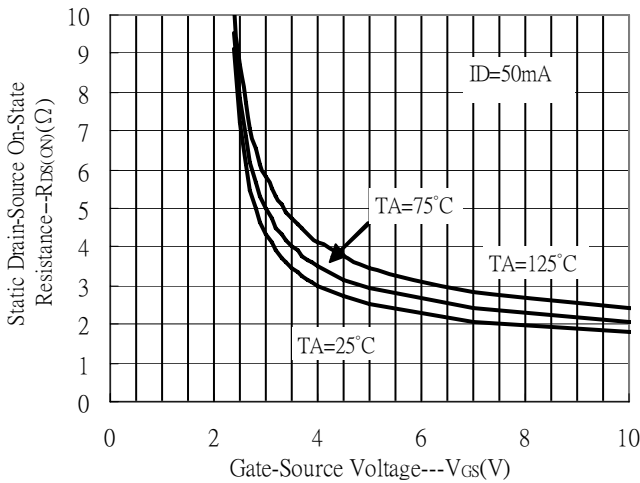
Static Drain-Source On-State Resistance vs Drain Current



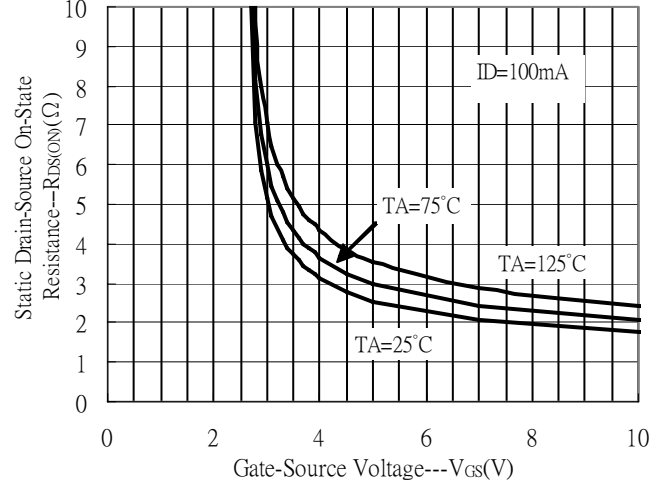
Static Drain-Source On-State Resistance vs Drain Current



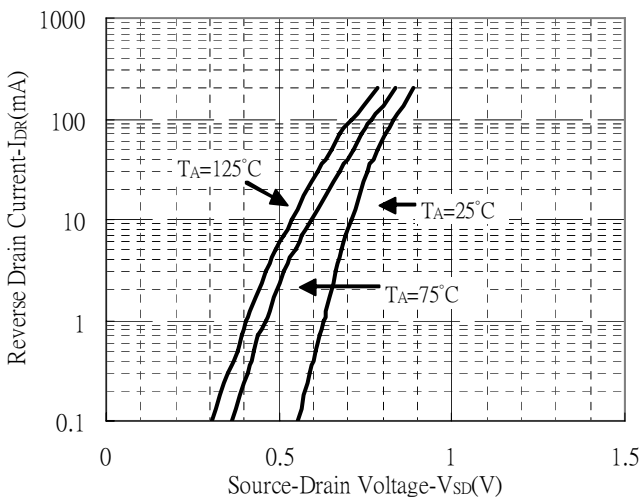
Static Drain-Source On-State Resistance vs Gate-Source Voltage



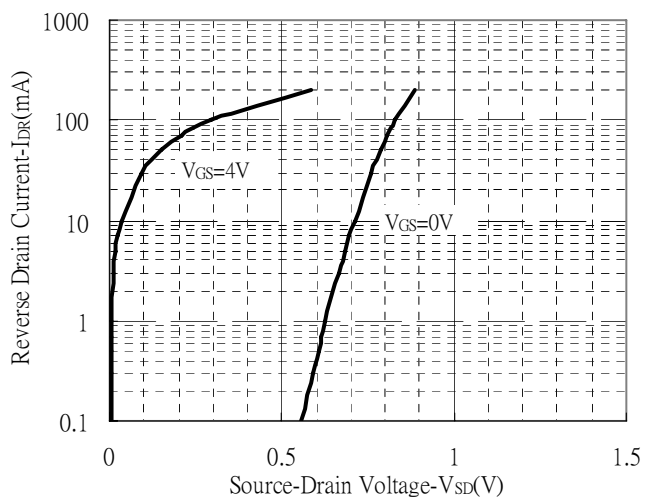
Static Drain-Source On-State Resistance vs Gate-Source Voltage



Reverse Drain Current vs Source-Drain Voltage(I)

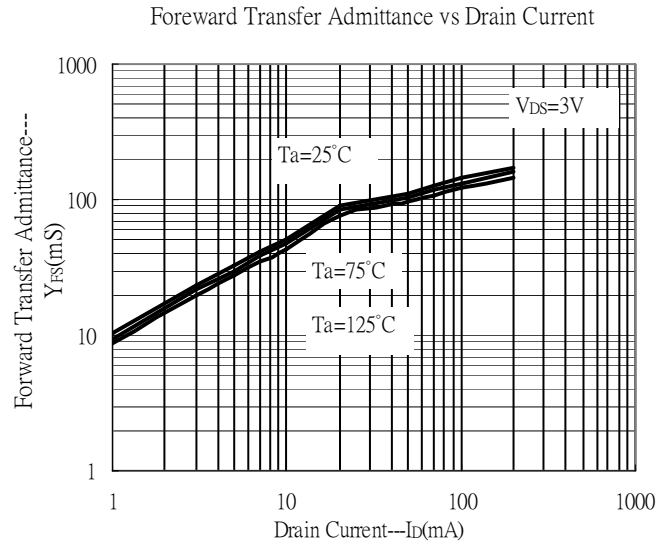
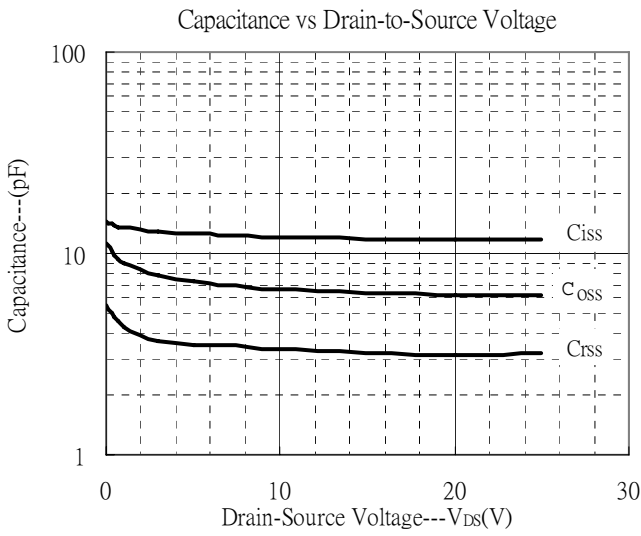


Reverse Drain Current vs Source-Drain Voltage(II)

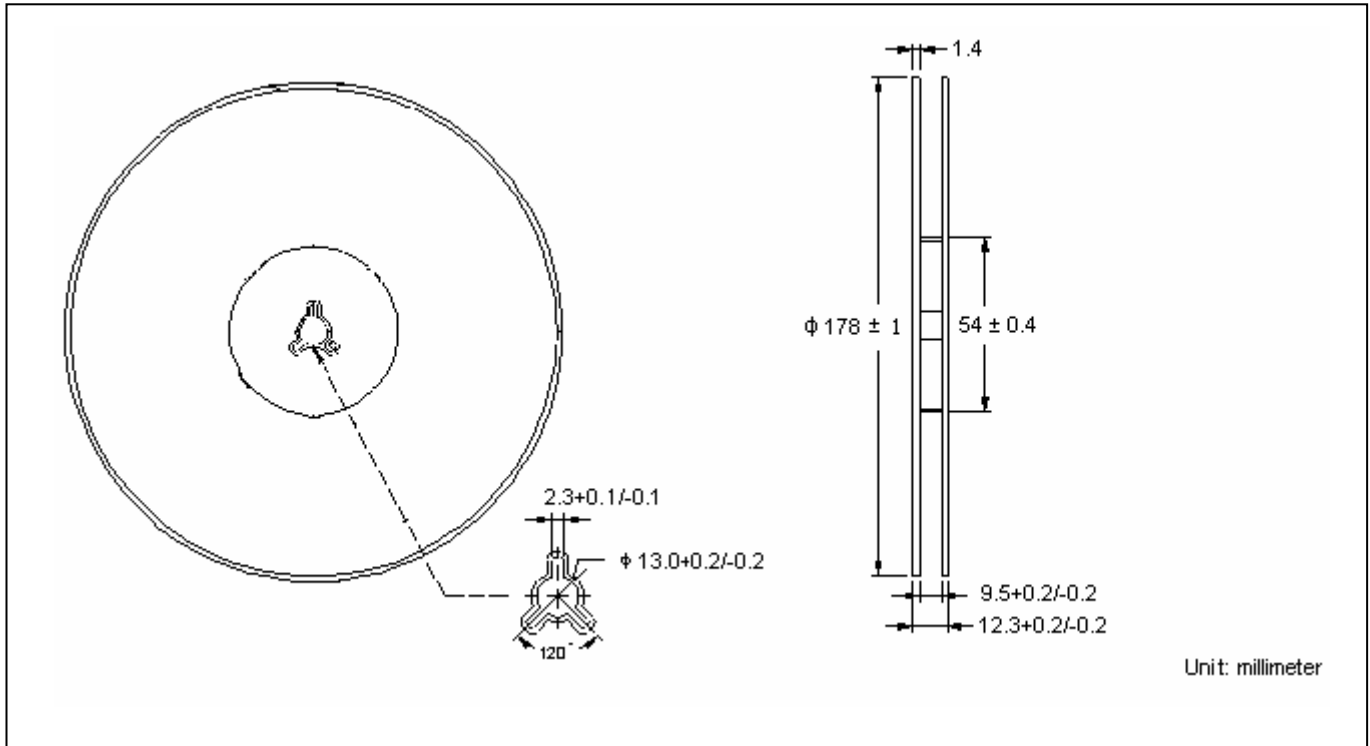




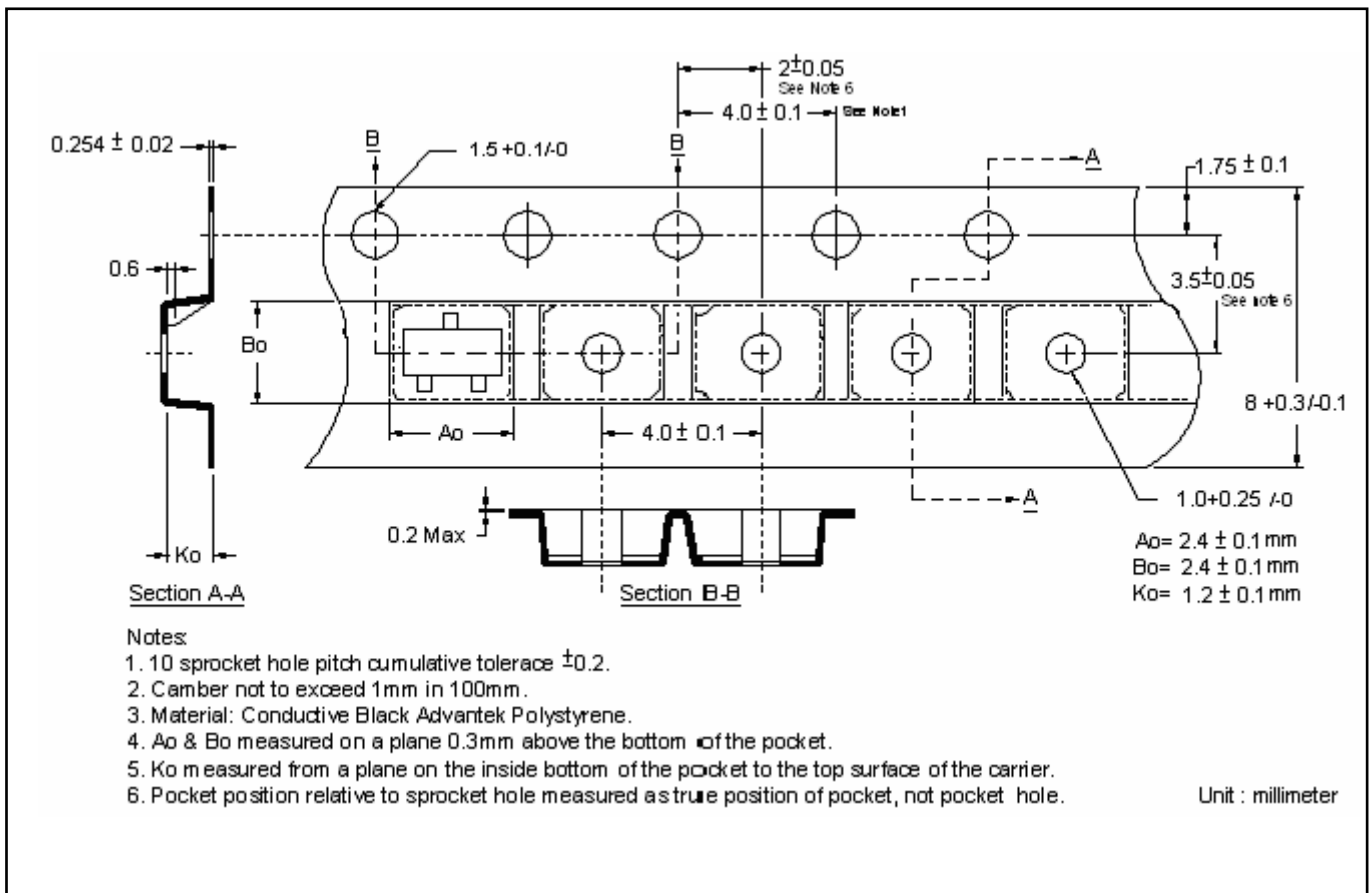
Typical Characteristics(Cont.)



Reel Dimension



Carrier Tape Dimension



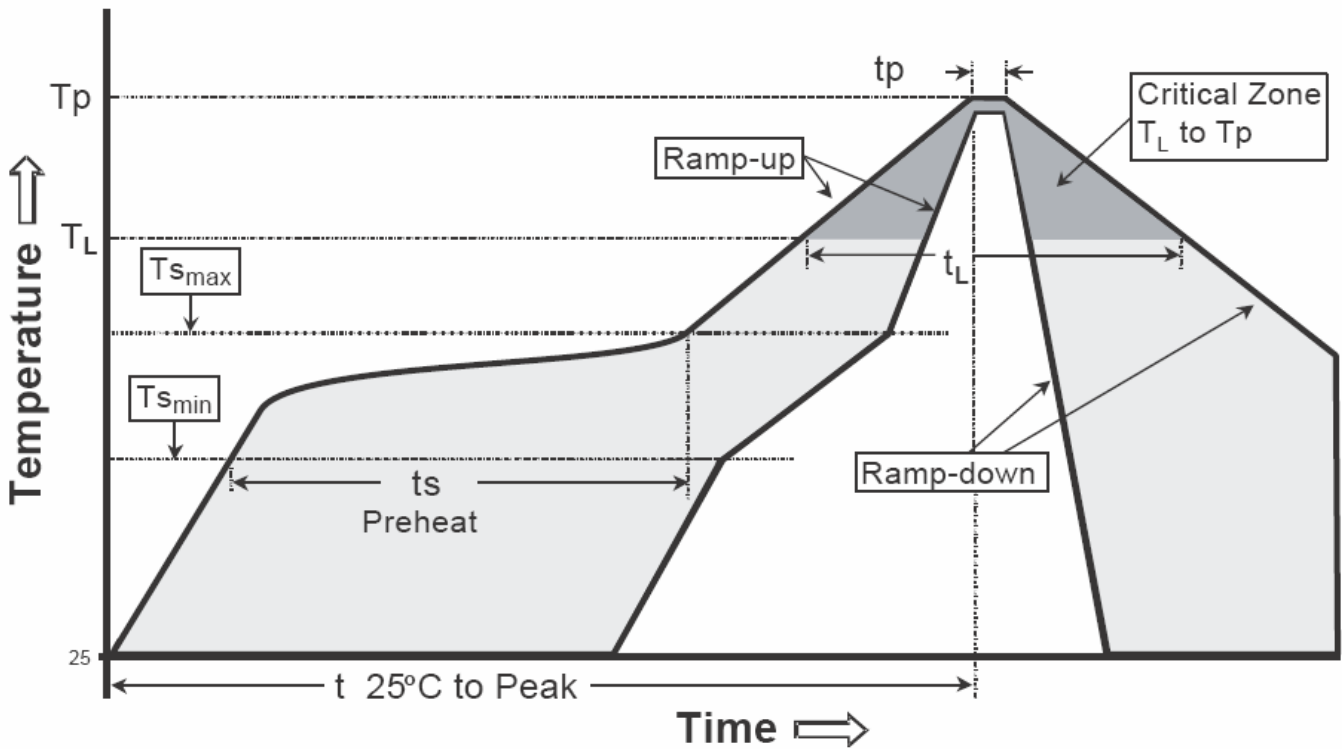
Notes:

1. 10 sprocket hole pitch cumulative tolerance ± 0.2 .
2. Camber not to exceed 1mm in 100mm.
3. Material: Conductive Black Advantek Polystyrene.
4. A_0 & B_0 measured on a plane 0.3mm above the bottom of the pocket.
5. K_0 measured from a plane on the inside bottom of the pocket to the top surface of the carrier.
6. Pocket position relative to sprocket hole measured as true position of pocket, not pocket hole.

Recommended wave soldering condition

| | | |
|-----------------|------------------|-----------------|
| Product | Peak Temperature | Soldering Time |
| Pb-free devices | 260 +0/-5 °C | 5 +1/-1 seconds |

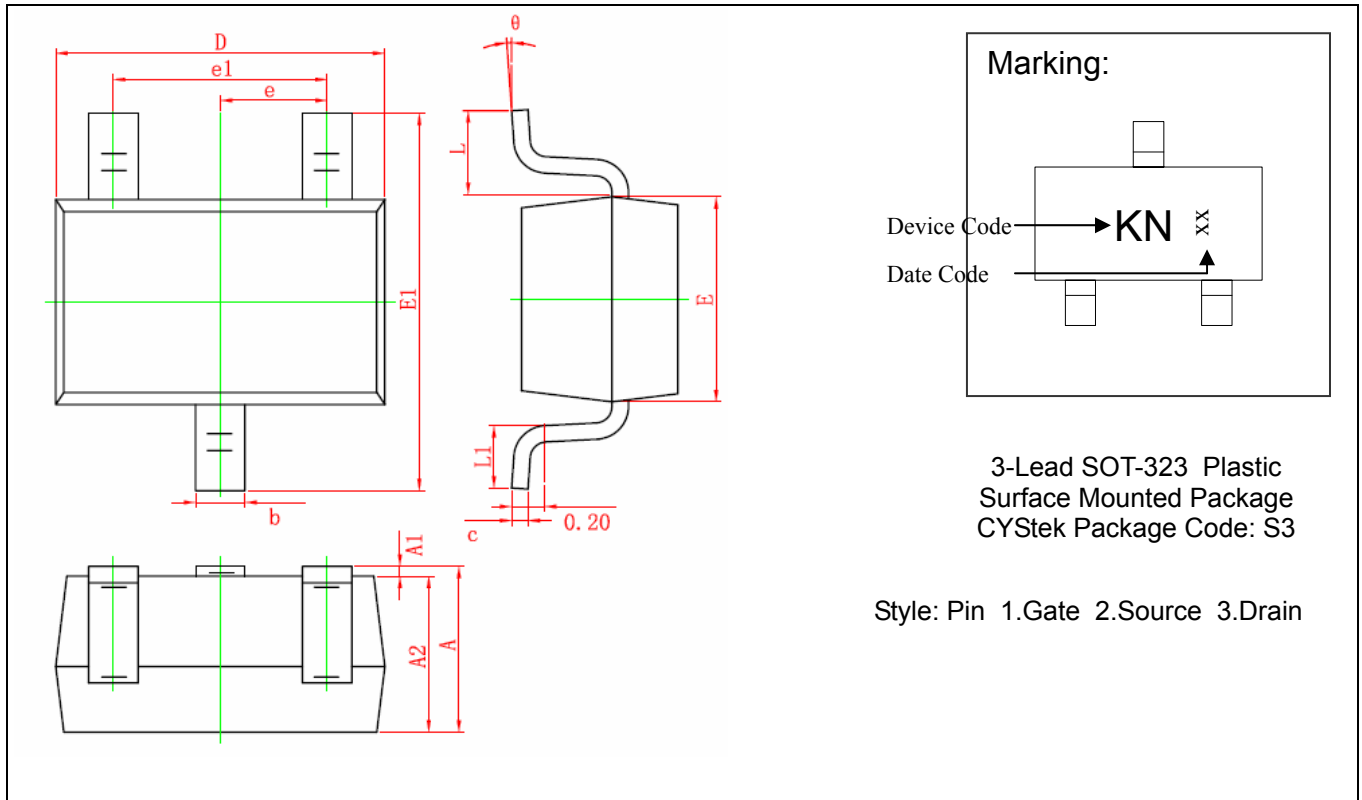
Recommended temperature profile for IR reflow



| Profile feature | Sn-Pb eutectic Assembly | Pb-free Assembly |
|---|-------------------------|------------------|
| Average ramp-up rate (T _{smax} to T _p) | 3°C/second max. | 3°C/second max. |
| Preheat | | |
| -Temperature Min(T _{s min}) | 100°C | 150°C |
| -Temperature Max(T _{s max}) | 150°C | 200°C |
| -Time(t _{s min} to t _{s max}) | 60-120 seconds | 60-180 seconds |
| Time maintained above: | | |
| -Temperature (T _L) | 183°C | 217°C |
| - Time (t _L) | 60-150 seconds | 60-150 seconds |
| Peak Temperature(T _P) | 240 +0/-5 °C | 260 +0/-5 °C |
| Time within 5°C of actual peak temperature(tp) | 10-30 seconds | 20-40 seconds |
| Ramp down rate | 6°C/second max. | 6°C/second max. |
| Time 25 °C to peak temperature | 6 minutes max. | 8 minutes max. |

Note : All temperatures refer to topside of the package, measured on the package body surface.

SOT-323 Dimension



| DIM | Millimeters | | Inches | | DIM | Millimeters | | Inches | |
|-----|-------------|-------|--------|-------|-----|-------------|-------|--------|-------|
| | Min. | Max. | Min. | Max. | | Min. | Max. | Min. | Max. |
| A | 0.900 | 1.100 | 0.035 | 0.043 | E1 | 2.150 | 2.450 | 0.085 | 0.096 |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 | e | 0.650 | TYP | 0.026 | TYP |
| A2 | 0.900 | 1.000 | 0.035 | 0.039 | e1 | 1.200 | 1.400 | 0.047 | 0.055 |
| b | 0.200 | 0.400 | 0.008 | 0.016 | L | 0.525 | REF | 0.021 | REF |
| c | 0.080 | 0.150 | 0.003 | 0.006 | L1 | 0.260 | 0.460 | 0.010 | 0.018 |
| D | 2.000 | 2.200 | 0.079 | 0.087 | θ | 0° | 8° | 0° | 8° |
| E | 1.150 | 1.350 | 0.045 | 0.053 | | | | | |

Notes: 1.Controlling dimension: millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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